

April 1995

6A, 400V - 600V Hyperfast Diodes

Features

- Hyperfast with Soft Recovery..... <30ns
- Operating Temperature +175°C
- Reverse Voltage Up To..... 600V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Description

RHRD640, RHRD650, RHRD660, RHRD640S, RHRD650S and RHRD660S are hyperfast diodes with soft recovery characteristics ($t_{RR} < 30ns$). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

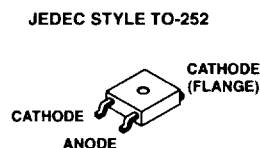
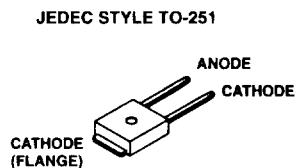
PACKAGE AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RHRD640	TO-251	RHR640
RHRD650	TO-251	RHR650
RHRD660	TO-251	RHR660
RHRD640S	TO-252	RHR640
RHRD650S	TO-252	RHR650
RHRD660S	TO-252	RHR660

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252 variant in tape and reel, e.g. RHRD660S9A.

Formerly developmental type TA49057.

Package



Symbol



Absolute Maximum Ratings $T_C = +25^\circ C$, Unless Otherwise Specified

	RHRD640 RHRD640S	RHRD650 RHRD650S	RHRD660 RHRD660S	UNITS
Peak Repetitive Reverse Voltage..... V_{RRM}	400	500	600	V
Working Peak Reverse Voltage..... V_{RWM}	400	500	600	V
DC Blocking Voltage..... V_R	400	500	600	V
Average Rectified Forward Current..... $I_{F(AV)}$ ($T_C = +152^\circ C$)	6	6	6	A
Repetitive Peak Surge Current..... I_{FSM} (Square Wave, 20kHz)	12	12	12	A
Nonrepetitive Peak Surge Current..... I_{FSM} (Halfwave, 1 Phase, 60Hz)	60	60	60	A
Maximum Power Dissipation..... P_D	50	50	50	W
Avalanche Energy (See Figures 10 and 11)..... E_{AVL}	10	10	10	mJ
Operating and Storage Temperature..... T_{STG}, T_J	-65 to +175	-65 to +175	-65 to +175	$^\circ C$

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HYPERFAST
SINGLE DIODES

Specifications RHRD640, RHRD650, RHRD660, RHRD640S, RHRD650S, RHRD660S

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	RHRD640, RHRD640S			RHRD650, RHRD650S			RHRD660, RHRD660S			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V_F	$I_F = 6\text{A}, T_C = +25^\circ\text{C}$	-	-	2.1	-	-	2.1	-	-	2.1	V
	$I_F = 6\text{A}, T_C = +150^\circ\text{C}$	-	-	1.7	-	-	1.7	-	-	1.7	V
I_R	$V_R = 400\text{V}, T_C = +25^\circ\text{C}$	-	-	100	-	-	-	-	-	-	μA
	$V_R = 500\text{V}, T_C = +25^\circ\text{C}$	-	-	-	-	-	100	-	-	-	μA
	$V_R = 600\text{V}, T_C = +25^\circ\text{C}$	-	-	-	-	-	-	-	-	100	μA
I_R	$V_R = 400\text{V}, T_C = +150^\circ\text{C}$	-	-	500	-	-	-	-	-	-	μA
	$V_R = 500\text{V}, T_C = +150^\circ\text{C}$	-	-	-	-	-	500	-	-	-	μA
	$V_R = 600\text{V}, T_C = +150^\circ\text{C}$	-	-	-	-	-	-	-	-	500	μA
t_{RR}	$I_F = 1\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	30	-	-	30	-	-	30	ns
	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	35	-	-	35	-	-	35	ns
t_A	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	16	-	-	16	-	-	16	-	ns
t_B	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	8.5	-	-	8.5	-	-	8.5	-	ns
Q_{RR}	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	45	-	-	45	-	-	45	-	nC
C_J	$V_R = 10\text{V}, I_F = 0\text{A}$	-	20	-	-	20	-	-	20	-	pF
$R_{\theta JC}$		-	-	3	-	-	3	-	-	3	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage ($p_w = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current.

t_{RR} = Reverse recovery time (See Figure 2), summation of $t_A + t_B$.

t_A = Time to reach peak reverse current (See Figure 2).

t_B = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 2).

Q_{RR} = Reverse recovery charge.

C_J = Junction capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

E_{AVL} = Controlled avalanche energy (See Figures 10 and 11).

p_w = pulse width.

D = duty cycle.

V_1 AMPLITUDE CONTROLS I_F
 V_2 AMPLITUDE CONTROLS dI_F/dt
 L_1 = SELF INDUCTANCE OF
 $R_4 + L_{LOOP}$

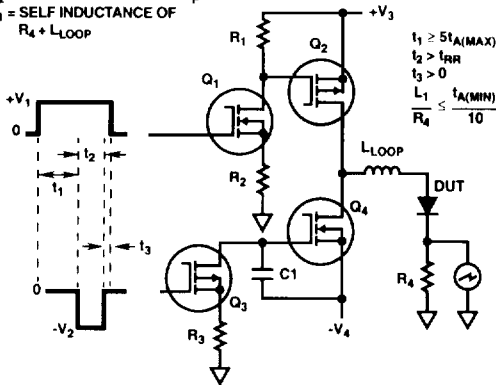


FIGURE 1. t_{RR} TEST CIRCUIT

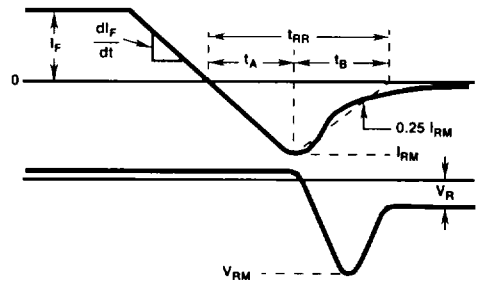


FIGURE 2. t_{RR} WAVEFORMS AND DEFINITIONS

Typical Performance Curves

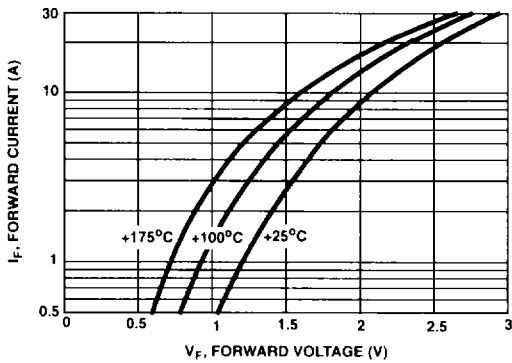


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

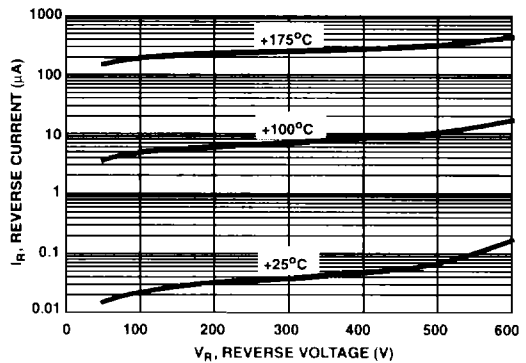


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

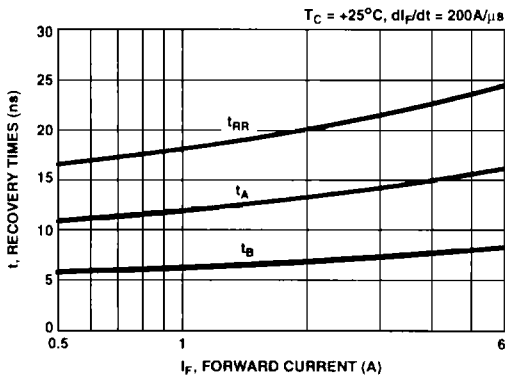


FIGURE 5. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +25°C

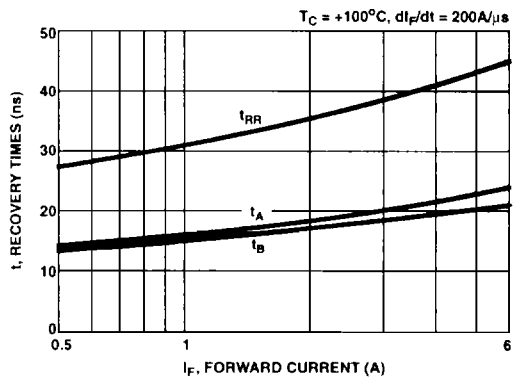


FIGURE 6. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +100°C

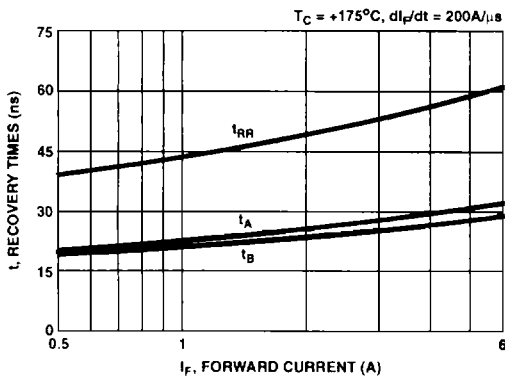


FIGURE 7. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +175°C

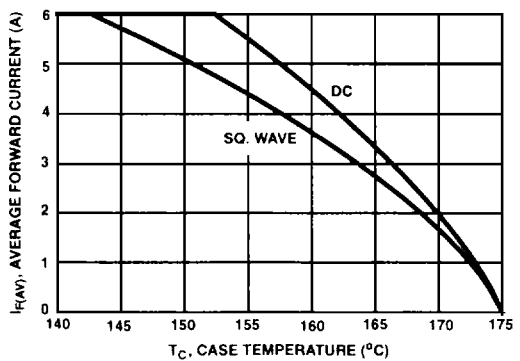


FIGURE 8. CURRENT DERATING CURVE FOR ALL TYPES

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Typical Performance Curves (Continued)

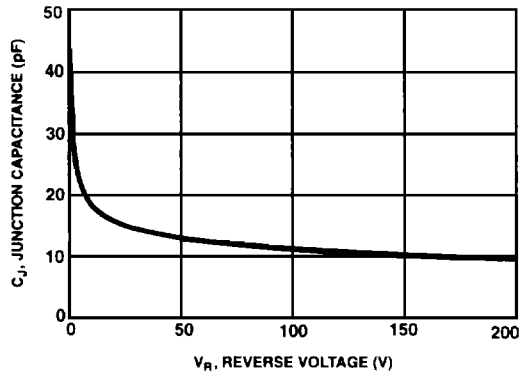


FIGURE 9. TYPICAL JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuit and Waveform

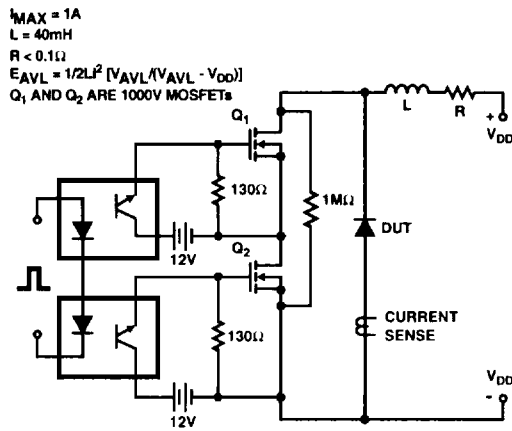


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

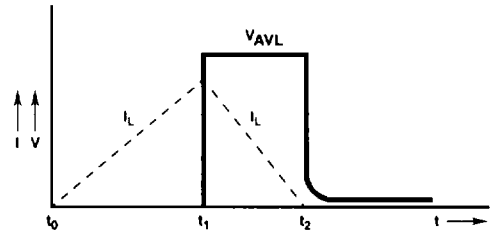


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS